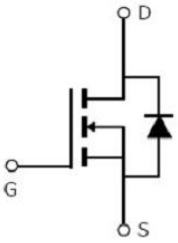
V_{DSS}	30V
R_{DS}(on)	10mΩ (typ.)
I_D	20A



Advanced MOSFET process technology
Special designed for PWM, load switching and general purpose applications
Ultra low on-resistance with low gate charge
Fast switching and reverse body recovery
150 operating temperature

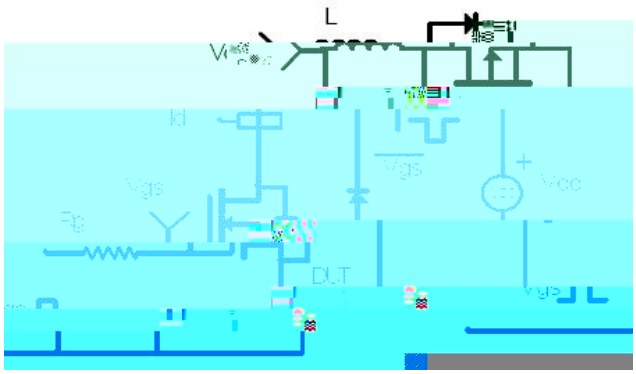
It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

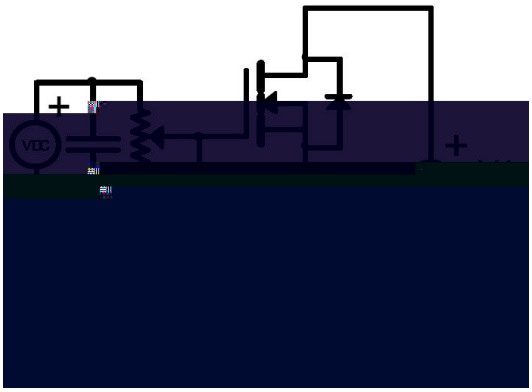
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	20	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	14	
I_{DM}	Pulsed Drain Current	80	
P_D @T_C = 25°C	Power Dissipation	62	W
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

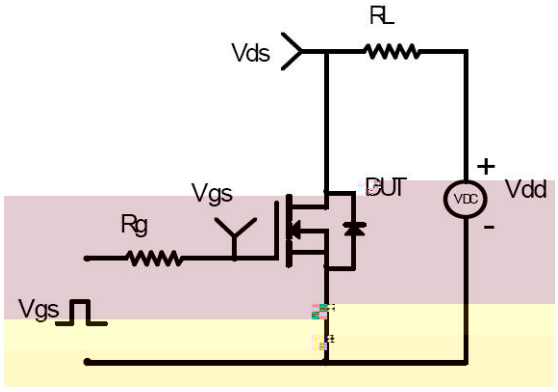
$R_{\theta JC}$	Junction-to-case	—	2	/W

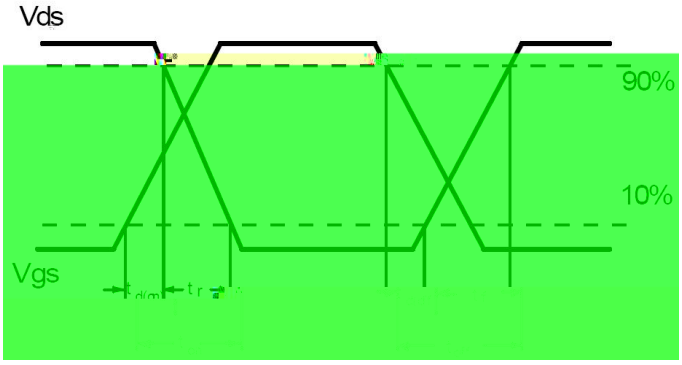
@T_A=25 unless otherwise specified

$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	30	—	—	V	V_{GS} = 0V, I_D = 250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	10	13	mΩ	V_{GS}=10V,I_D = 15A
		—	16	22.5		V_{GS}=4.5V,I_D = 10A
$V_{GS(th)}$	Gate threshold voltage	1	—	2.2	V	V_{DS} = V_{GS}, I_D = 250μA
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	V_{DS} = 30V,V_{GS} = 0V
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS} =20V
		—	—	-100		V_{GS} = -20V
C_{iss}	Input capacitance	—	805	—	pF	V_{GS} = 0V V_{DS} = 15V f =

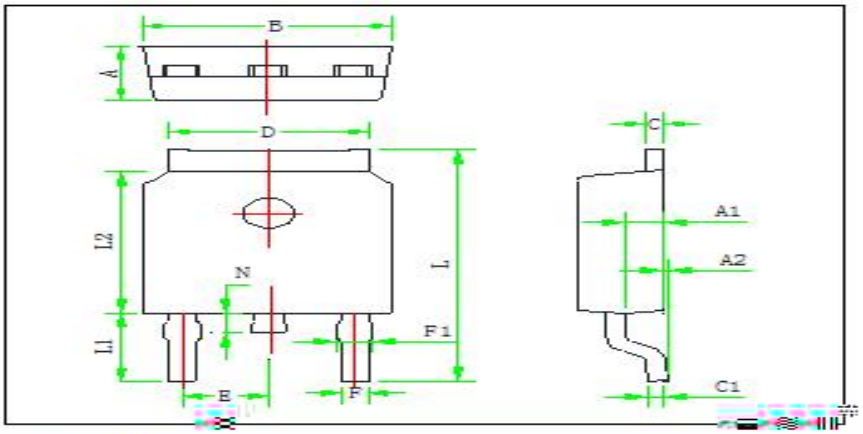








Calculated continuous current based on maximum allowable junction temperature.
Repetitive rating; pulse width limited by max. junction temperature.
The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.



Symbol	Min	Typ	Max
A	2.20	2.30	2.40
A1	0.91	1.01	1.11
A2	0.05	0.15	0.25
B	6.45	6.60	6.75
C	0.45	[illegible]	[illegible]
C1	[illegible]	[illegible]	0.58
D	5.12	5.32	5.52
E		2.286 TYP	
F	0.66	0.76	0.86
F1	0.66	0.86	1.06
L	9.60	9.90	10.20
L1	2.6	2.8	3.0
L2	5.95	6.10	6.25
N	0.60	0.80	1.00

- Any and all Silikron products described or contained herein do not have specifications that can handle